



HTIP122

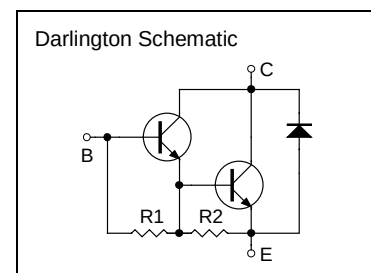
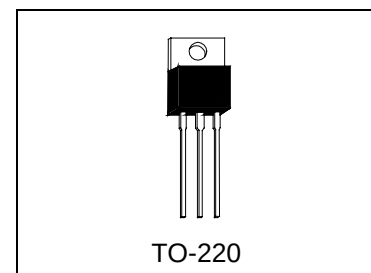
NPN EPITAXIAL PLANAR TRANSISTOR

Description

The HTIP122 is designed for use in general purpose amplifier and low-speed switching applications.

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$)

- Maximum Temperatures
 - Storage Temperature $-55 \sim +150^\circ\text{C}$
 - Junction Temperature $+150^\circ\text{C}$ Maximum
- Maximum Power Dissipation
 - Total Power Dissipation ($T_C=25^\circ\text{C}$) 65 W
 - Total Power Dissipation ($T_A=25^\circ\text{C}$) 2 W
- Maximum Voltages and Currents
 - BV_{CBO} Collector to Base Voltage 100 V
 - BV_{CEO} Collector to Emitter Voltage 100 V
 - BV_{EBO} Emitter to Base Voltage 5 V
 - I_C Collector Current (Continuous) 5 A
 - I_C Collector Current (Peak) 8 A



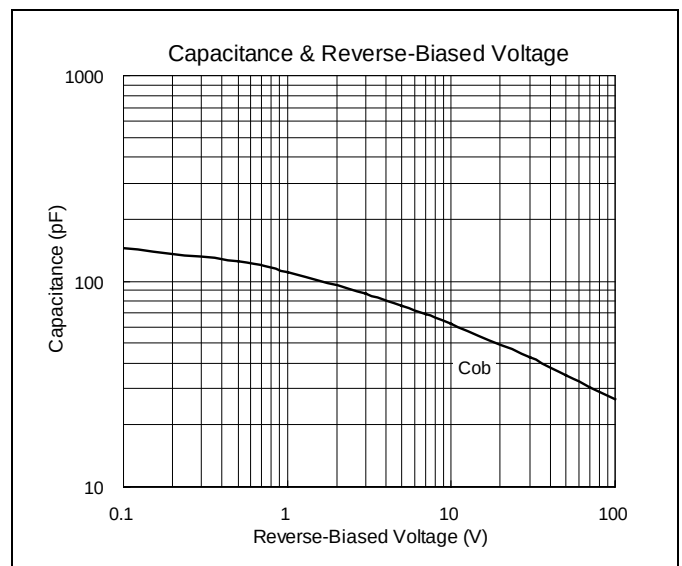
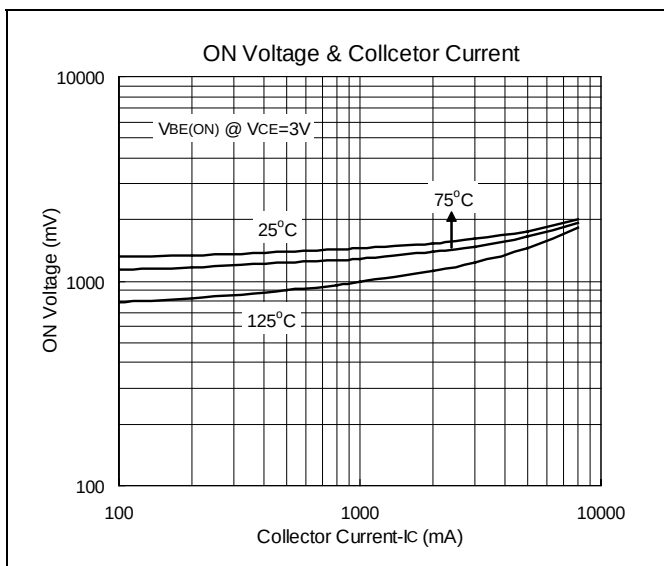
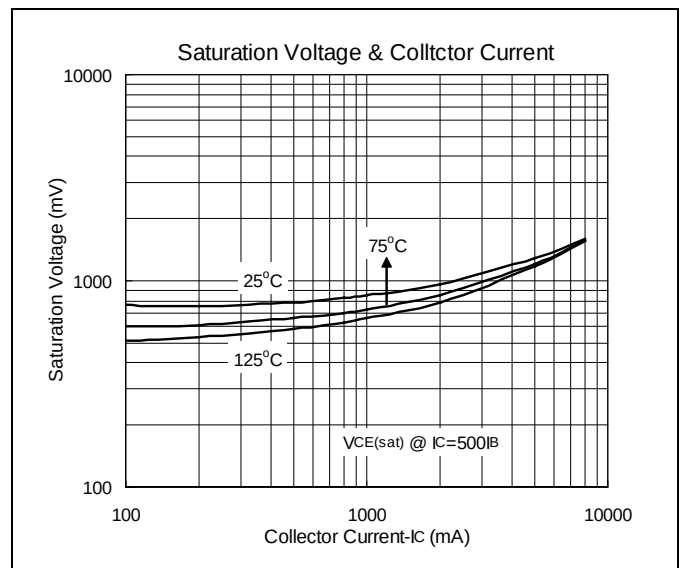
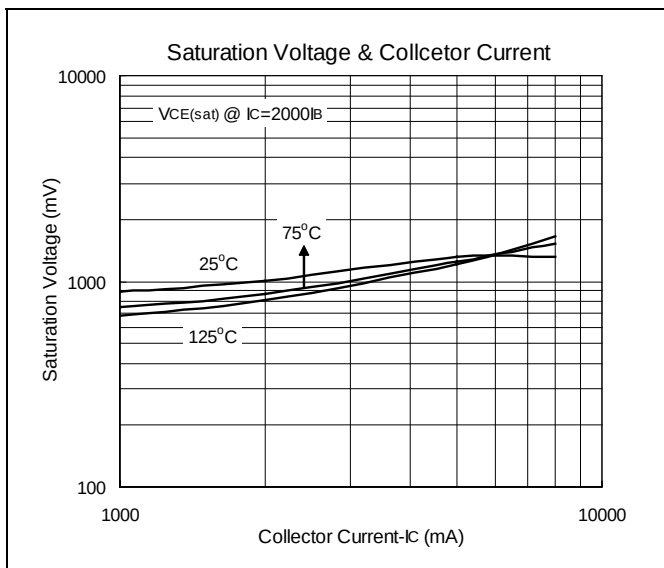
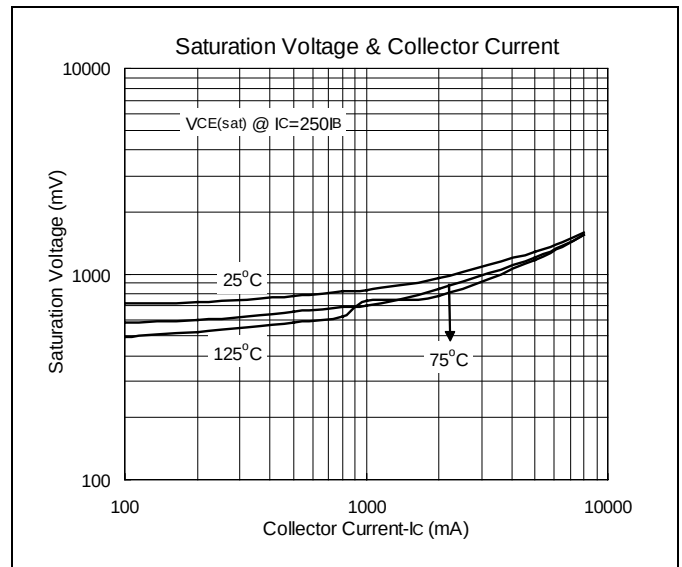
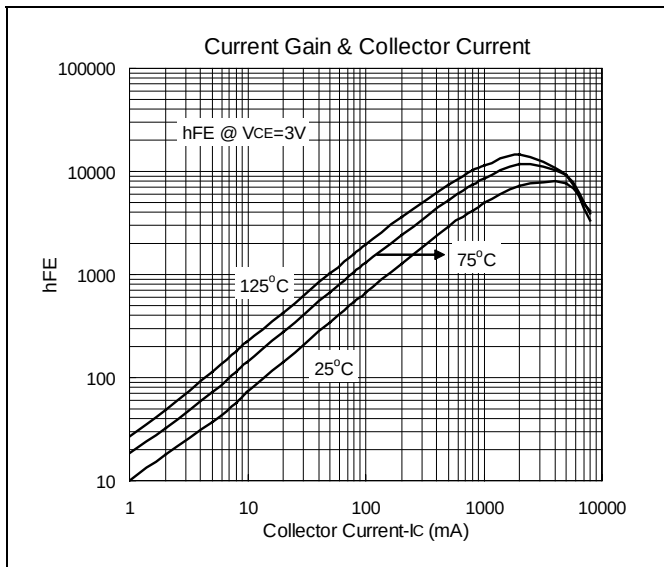
Electrical Characteristics ($T_A=25^\circ\text{C}$)

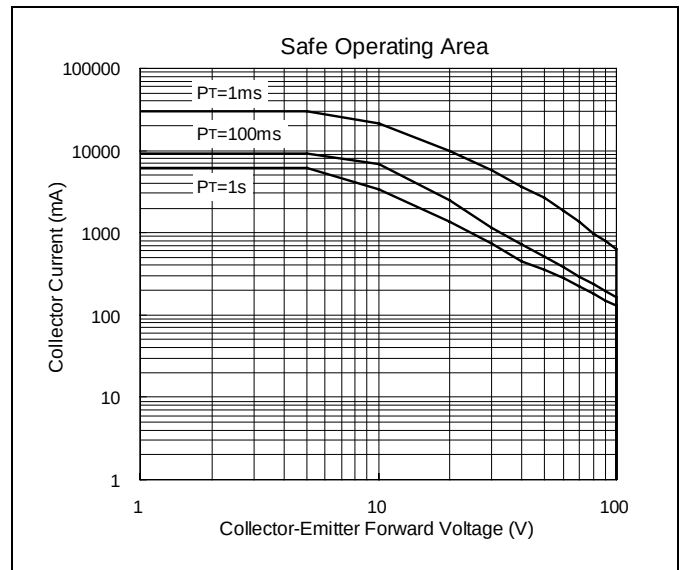
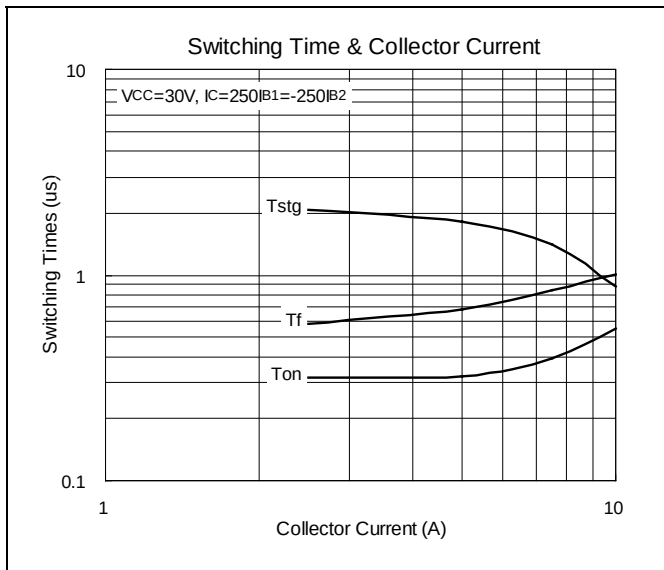
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	100	-	-	V	$I_C=1\text{mA}$, $I_E=0$
I_{CBO}	-	-	200	μA	$V_{CB}=100\text{V}$
I_{CEO}	-	-	500	μA	$V_{CE}=100\text{V}$
I_{EBO}	-	-	2	mA	$V_{EB}=5\text{V}$
$*V_{CE(sat)1}$	-	-	2	V	$I_C=3\text{A}$, $I_B=12\text{mA}$
$*V_{CE(sat)2}$	-	-	4	V	$I_C=5\text{A}$, $I_B=20\text{mA}$
$*V_{BE(on)}$	-	-	2.5	V	$I_C=3\text{A}$, $V_{CE}=3\text{V}$
$*h_{FE1}$	1	-	-	K	$I_C=0.5\text{A}$, $V_{CE}=3\text{V}$
$*h_{FE2}$	1	-	-	K	$I_C=3\text{A}$, $V_{CE}=3\text{V}$
Cob	-	-	200	pF	$V_{CB}=10\text{V}$, $f=1\text{MHz}$

*Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$



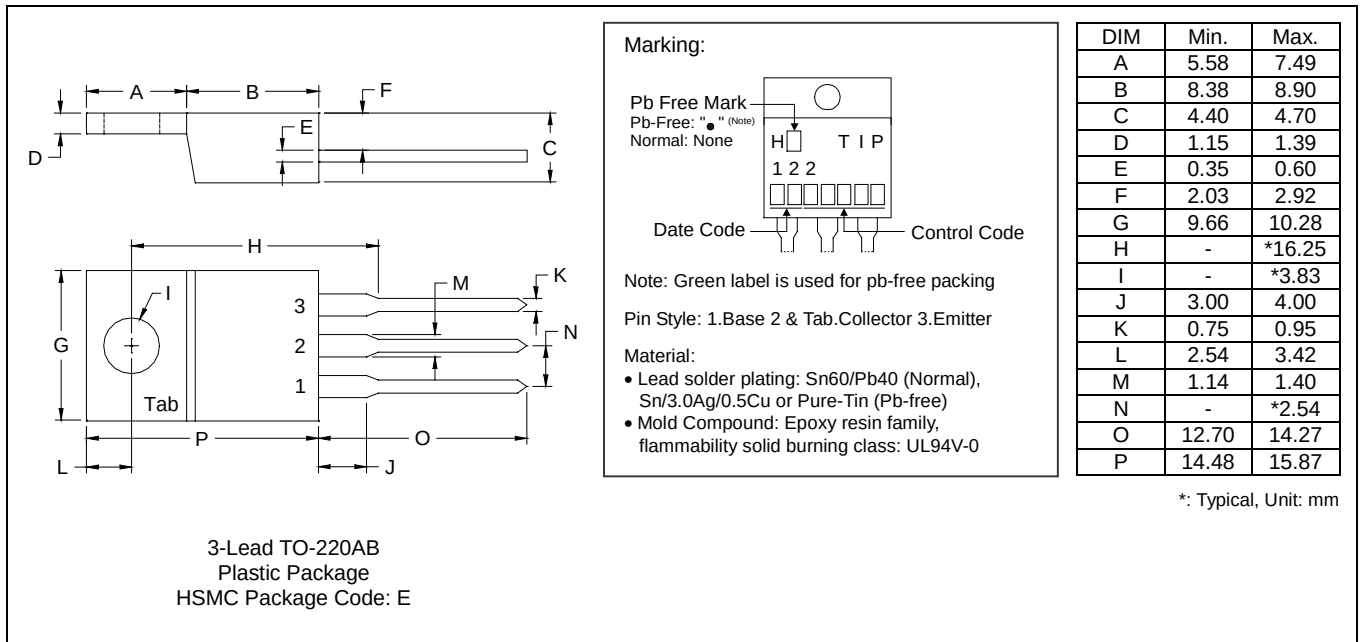
Characteristics Curve







TO-220AB Dimension



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Head Office And Factory:

- **Head Office** (Hi-Sincerity Microelectronics Corp.): 10F., No. 61, Sec. 2, Chung-Shan N. Rd. Taipei Taiwan R.O.C.
Tel: 886-2-25212056 Fax: 886-2-25632712, 25368454
- **Factory 1:** No. 38, Kuang Fu S. Rd., Fu-Kou Hsin-Chu Industrial Park Hsin-Chu Taiwan. R.O.C
Tel: 886-3-5983621~5 Fax: 886-3-5982931

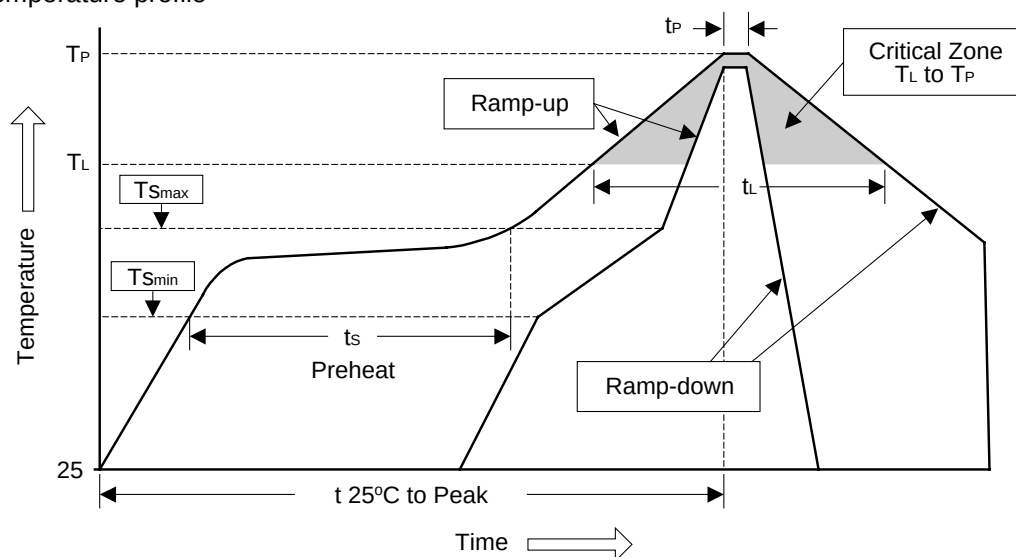


Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%

2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{smin})	100°C	150°C
- Temperature Max (T_{smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec